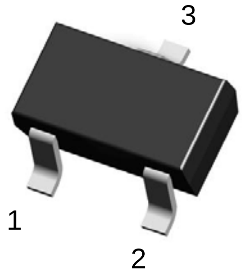
P-Channel Enhancement-Mode MOSFET (-20V, -4A)

PRODUCT SUMMARY		
V_{DSS}	I_D	$R_{DS(on)}$ (m-ohm) Max
-20V	-4A	43 @ V_{GS} = -4.5V,I_D=-4A
		54 @ V_{GS} = -2.5V,I_D=-4A
		73 @ V_{GS} = -1.8V,I_D=-2A

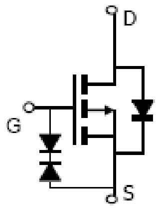
Features

- Super high dense cell trench design for low RDS(on).
- Rugged and reliable.
- ESD Rating:3000V HBM
- Ordering information：KF3415E（Lead（Pb）-free）
  KF3415E-G（Lead（Pb）-free and halogen-free）



KF3415 E Pin Assignment & Symbol

3-Lead Plastic **SOT-23-3L**
Pin 1: Gate 2: Source 3: Drain



Absolute Maximum Ratings (T_A=25°C, unless otherwise noted)

Symbol	Parameter	Ratings	Units
V_{DS}	Drain-Source Voltage	-20	V
V_{GS}	Gate-Source Voltage	±8	V
I_D	Drain Current @T_A=25°C	-4	A
	Drain Current @T_A=70°C	-3.5	
I_{DM}	Drain Current (Pulsed) [*1]	-30	A
P_D	Total Power Dissipation @T_A=25°C	1.4	W
	Total Power Dissipation @T_A=70°C	0.9	
T_j, T_{stg}	Operating Junction and Storage Temperature Range	-55 to +150	°C
$R_{\theta JA}$	Thermal Resistance Junction to Ambient (t≤10s)	90	°C/W
	Thermal Resistance Junction to Ambient (Steady-State)	125	
$R_{\theta JL}$	Thermal Resistance Junction to Lead (Steady-State)	60	°C/W

a: Surface Mounted on FR4 Board , t ≤ 5sec .
b: 1 Pulse Test: Pulse width ≤ 300us , Duty Cycle ≤ 2% .